<u>Novel Methods for Reducing</u> <u>UHP Gas Usage in Fabs: Back Diffusion</u> <u>Minimization</u>

Customized Project; Sponsored by Intel

<u>**PI**</u>:

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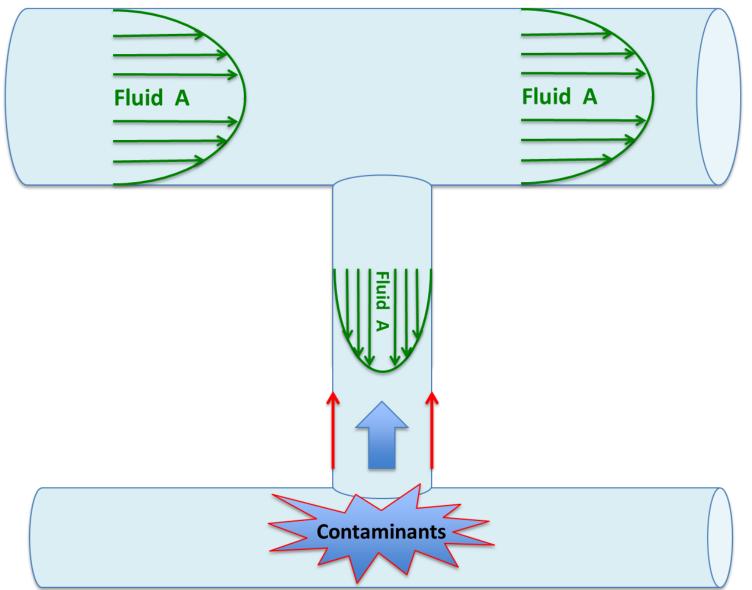
<u>Co-PI:</u>

• Carl Geisert, Sr. Principal Engineer, Intel

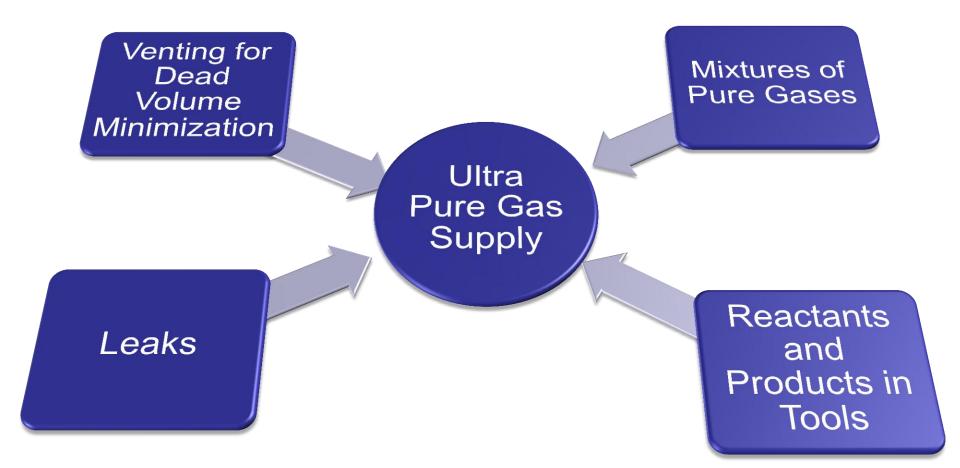
Graduate Student:

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Back Diffusion Sources and Mechanisms



Back Diffusion Sources and Mechanisms



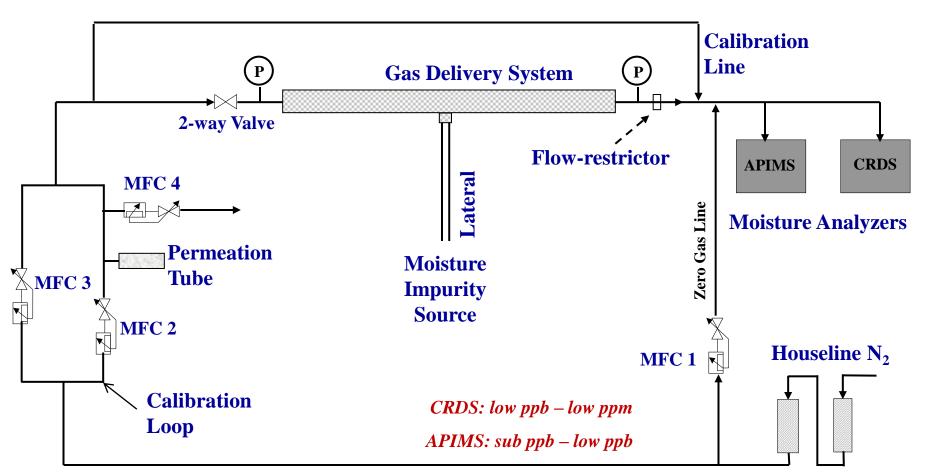
Objectives

- Developing operational parameters that will minimize back diffusion of impurities into fluidic distribution systems.
- Developing and validating a process simulator that can help industry design and operate systems while minimizing back diffusion, gas usage, and system dead volumes.
- Develop a better understanding of back diffusion since little is known or has been published on the subject.

Motivation and ESH Impact

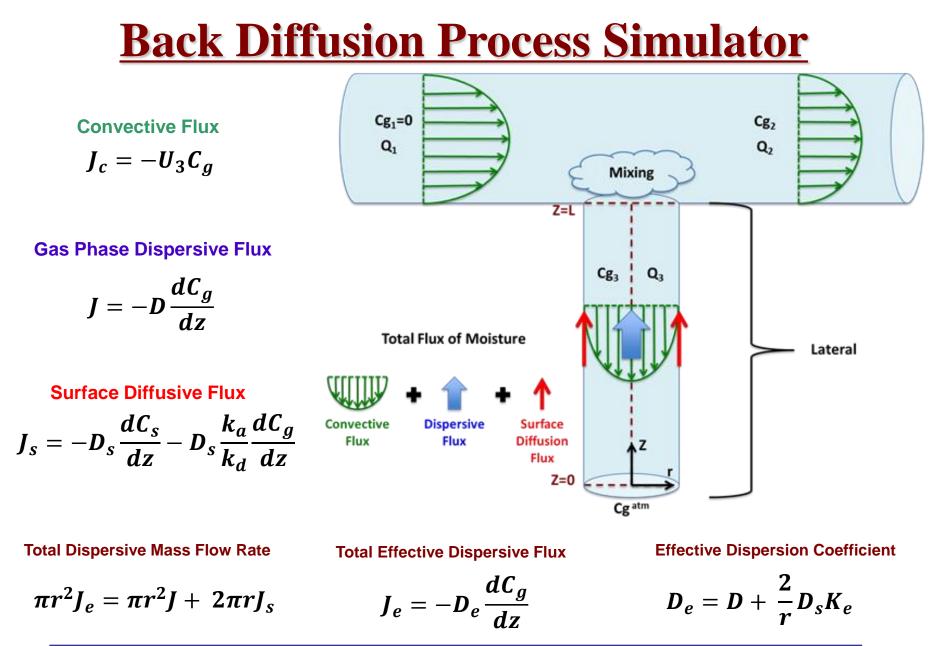
• Contamination of gas distribution systems during normal operation results in major wasting of materials, energy, and valuable tool operation time.

Experimental Testbed Laterals Added to the Main Line



Multistage Gas Purifier System

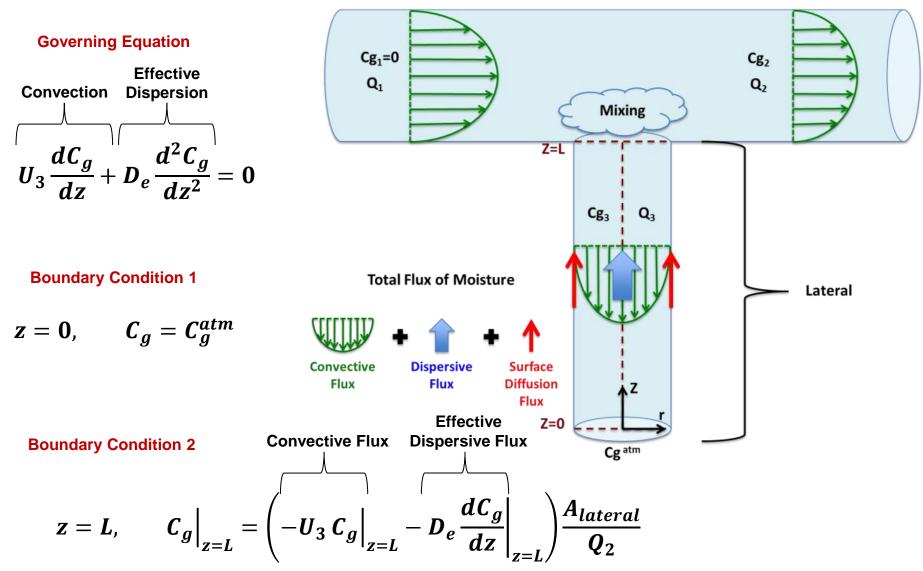
Gas distribution systems with different sizes and geometries were fabricated and provided by Intel



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Back Diffusion Process Simulator



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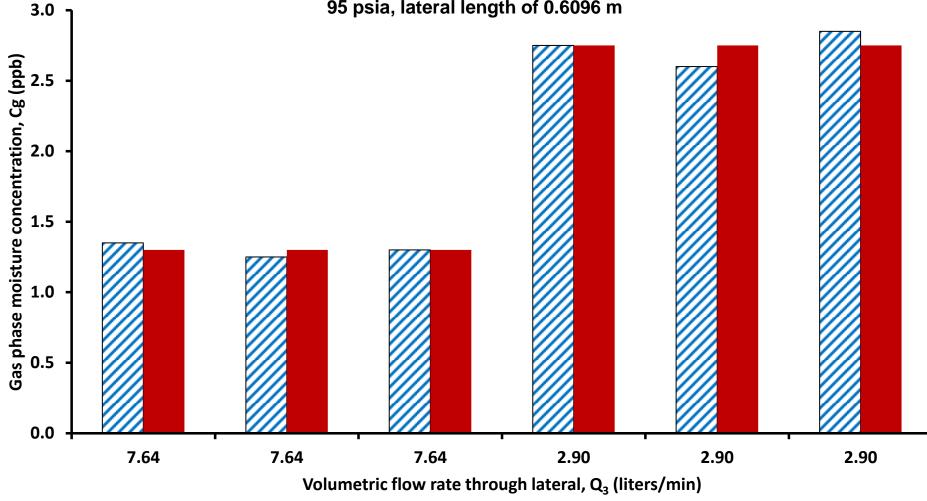
Process Simulator Verification

Simulator Prediction

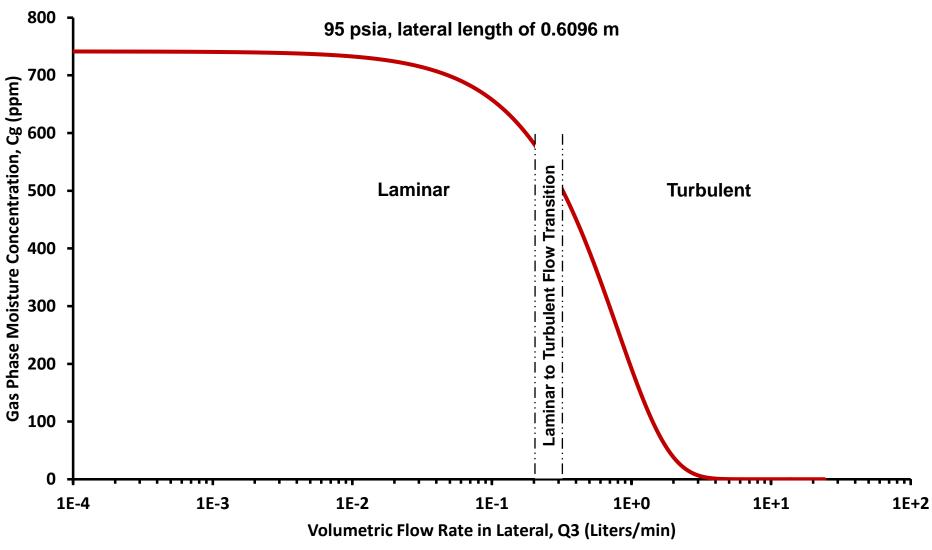
Experimental Results

Model Prediction

95 psia, lateral length of 0.6096 m

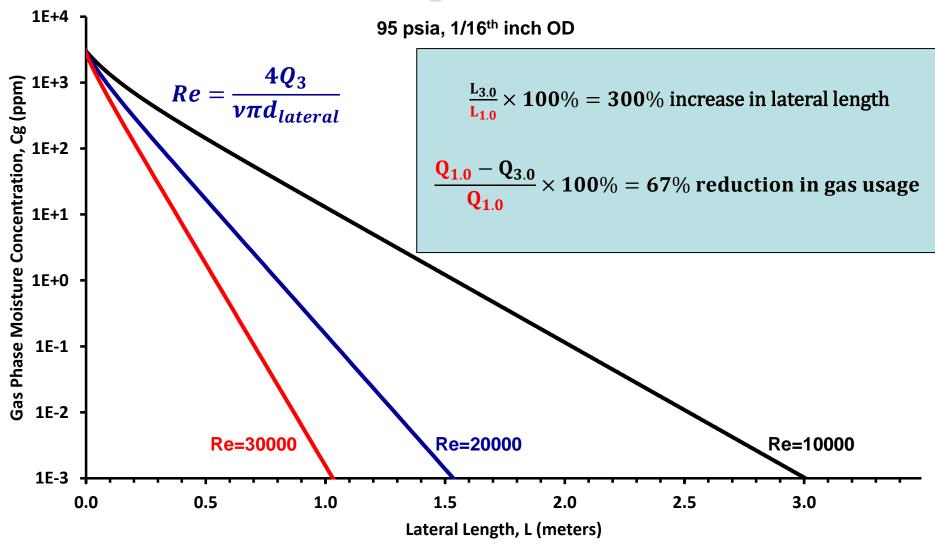


Effect of Flow Rate on Gas Phase Moisture



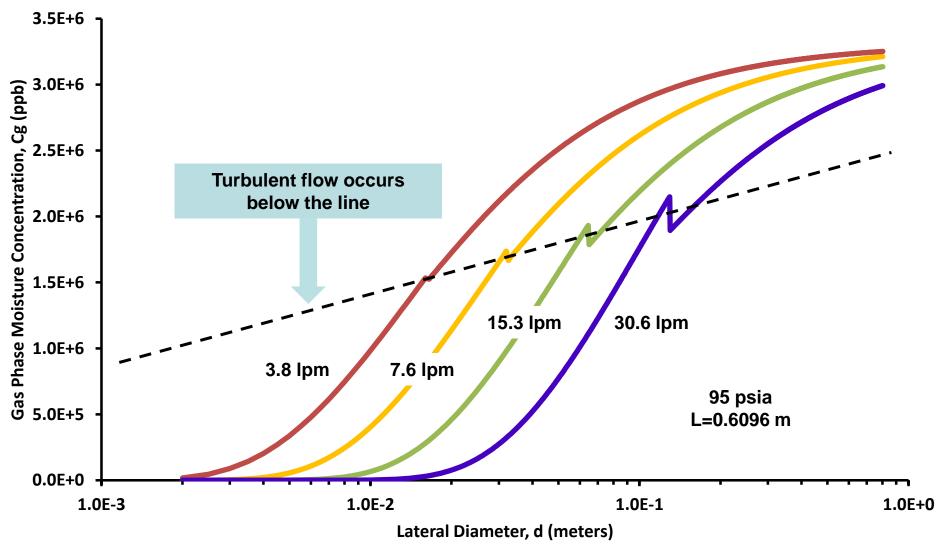
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Effect of Lateral Length on Gas Phase Moisture

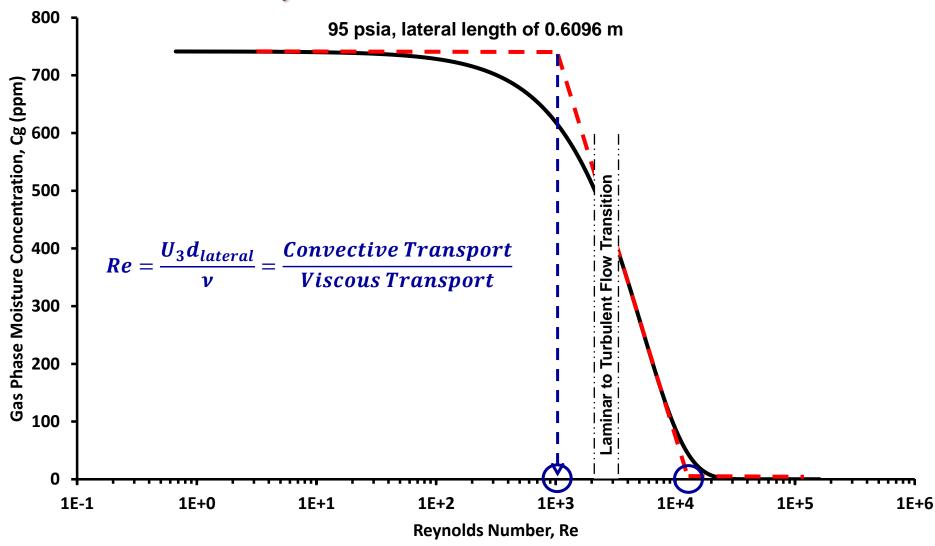


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Effect of Lateral Diameter on Gas Phase Moisture

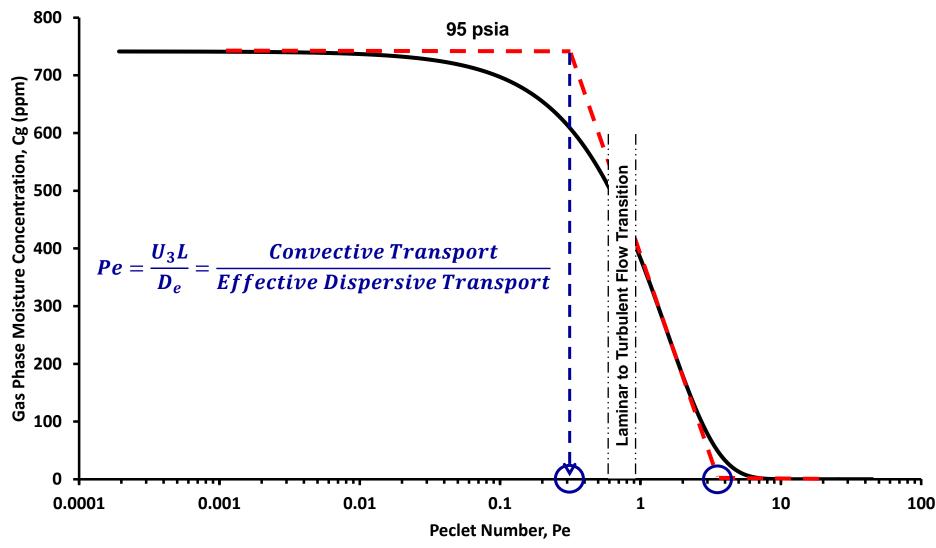


Effect of Reynolds Number on Gas Phase Moisture

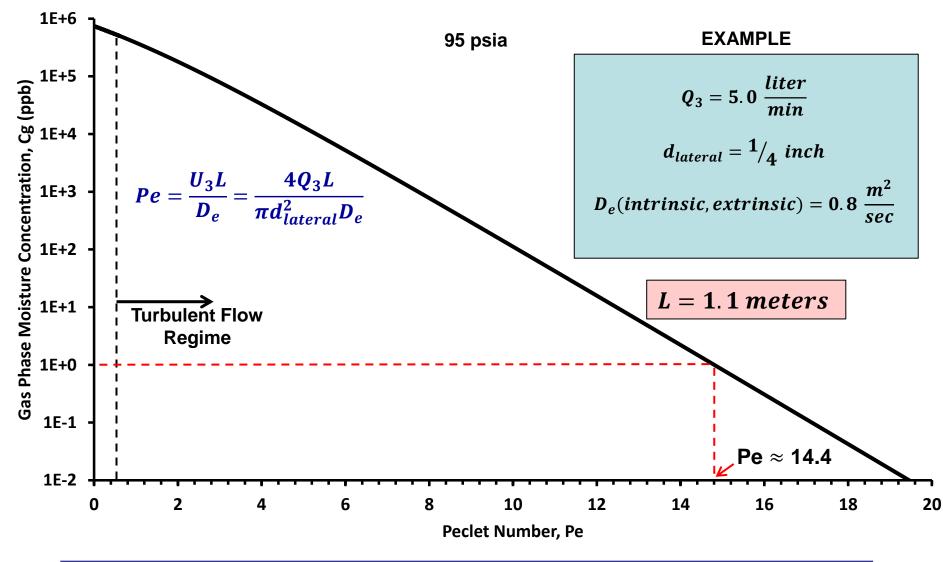


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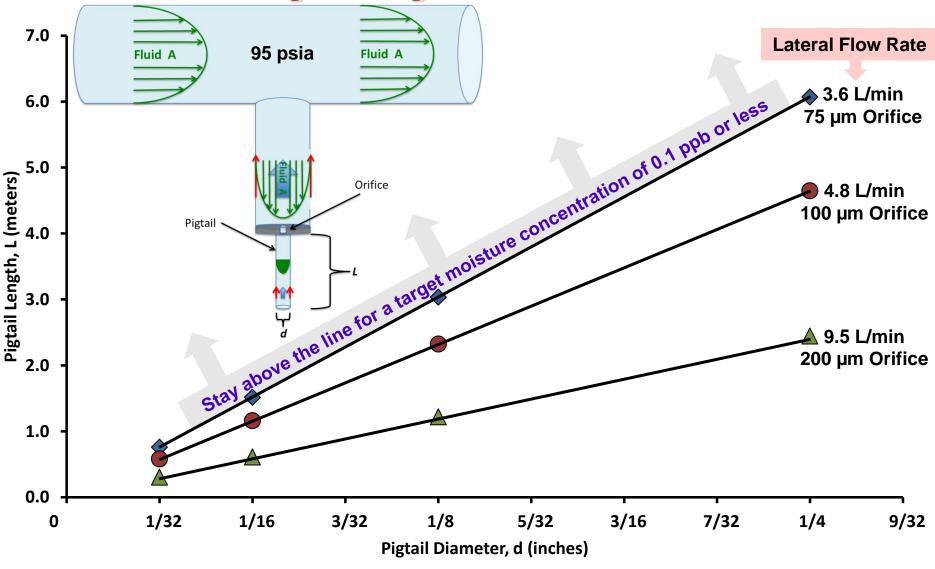
Effect of Peclet Number on Gas Phase Moisture



Effect of Peclet Number on Gas Phase Moisture



Pigtail Length and Diameters



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<u>Highlights</u>

- The experimental approach allowed for the observation of back diffusion in an adjustable and controllable manner.
- The process model accurately predicted experimental results and was invaluable in performing parametric studies.
- The moisture contamination due to back diffusion was a strong function of lateral diameter, length, and gas flow rate through the lateral.
- Characteristic groups were identified that allowed us present generalized correlations that would help in the design and operation of UHP fluidic systems being exposed to a source of contamination
- This methodology was expanded to include an orifice and pigtail in series and was effective in determining a design that will safeguard against the back diffusion of impurities into both bulk and process gases.

Industrial Interactions and Future Plans

- Continue our work with Intel on novel impurity control strategies to reduce gas usage
- Making the process simulator available to industry
- Extend the present study to other fluids, contaminants, and components

Acknowledgements

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